rm PTO-1449	Duche ( Hamber (Cpains)		Helderson Homen		
	TSMC-01-03	78	10/682,	952	
THEORYATION DISCLOSURE CITATION IN AN APPLICATION  (Light suveral showls if nocessary)	Arracon Varia P D 1 1				
IN AN APPLICATION	FHING Date /	Extra Con-Rey Peng et al.			
	10/09	03			
U. S. PA	TENT DOCUMENTS				
U. S. PAT	ונגעונ	CUL	mecri	אראים פינג	
	<del> </del>				
		-	_	<del></del>	
	·				
	77.7.7.1				
<del></del>		_	<del></del>		
		_		<del></del>	
		_	-		
		1	_		
			1		
FOREIGN P	PATENT DOCUMENT	S	•		
OCCURENT NUMBER DATE C	COUNTRY	cuss	รบขณะเ	Translation YES NO	
	·		-	YES NO	
			-		
		}			
		-			
		7			
	CUMENTS (Including A				
On-Chip Eso Protection D					
	ilican Diodes	in Sul	o a wante	~ micron	
1/ Using Volucrustalline S				_	
Mising Polycrystalline S	Rocealina	1000 F	Electrical	Questre	
Prosess, Chang and Ker	, Proceedings			Querstres	
Prosess, Chang and Ker	r, Proceedings				
Prosess, Chang and Ker					
Prosess, Chang and Ker					
Process, Chang and Ker Electrostatic Discharge S	grop., TEEE, NEWY				
Prosess, Chang and Ker					

EXAMINER: Initial infectation considered, whether or not citation is in conformance with MPEP 4 609; Draw line through citation if not in conformance and not considered, include copy of this form with next communication to the applicant

EXAMINER: Antial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include conv of this form with next communication to the applicant